

Silicon Rf Power Mos Fet Discrete Rd70huf2

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silicon rf power mos fet discrete rd70huf2 rf parts

rd70huf2 is mos fet type transistor specifically designed for vhf uhf rf power amplifiers applications features supply with tape and reel 500 units per reel employing mold package high power and high efficiency pout 75w typ drain effi 64 typ vds 12 5vidq 1 0apin 5 5wf 530mhz pout 84w typ drain effi 74 typ vds 12 5vidq 1 0apin 4 0wf 175mhz 4

silicon rf power mos fet discrete rd70hvf1

silicon rf power mos fet discrete rd70hvf1 rohs compliance silicon mosfet power transistor 175mhz 70w 520mhz 50w description rd70hvf1 is a mos fet type transistor specifically designed for vhf uhf high power amplifiers applications features high power and high gain pout 70w gp 10 6db vdd 12 5v f 175mhz pout 50w gp 7 0db vdd 12 5v f

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website**

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rd70huf2 mitsubishi electric us inc semiconductors and mitsubishi electric s lineup of high power si mos fet discrete and module products are suitable for frequency ranges from 30mhz to 1ghz and output power levels up to 100w key features high power gain and high efficiency integrated gate protection diode designed for vhf uhf rf power amplifier

applications specifications

silicon rf devices rf high power mos fets discrete rd70huf2

silicon rf devices rf high power mos fets discrete rd70huf2 parameter level value unit supply situation in production drain voltage typ

silicon rf power mos fet

discrete rd70hvf1 rf parts

description rd70hvf1 is a mos fet type transistor specifically designed for vhf uhf high power amplifiers applications outline drawing 25 0 0 3 7 0 0 511 0 0 3 features 1 4 c2 high power and high gain pout 70w gp 10 6db vdd 12 5v f 175mhz pout 50w gp 7 0db vdd 12 5v f 520mhz high efficiency 60 typ on vhf band